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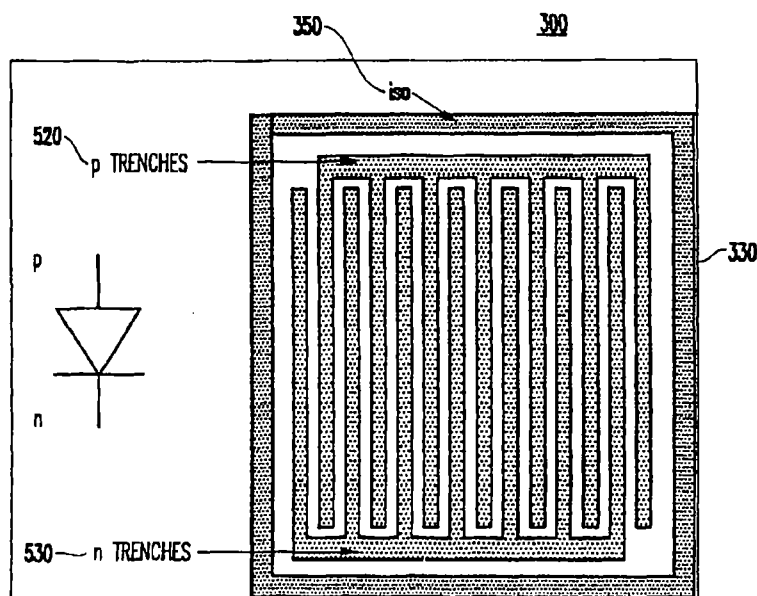
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(54) Title: SILICON-ON-INSULATOR (SOI) TRENCH PHOTODIODE AND METHOD OF FORMING SAME



(57) Abstract: A semiconductor device (and method for forming the device) includes a silicon-on-insulator (SOI) wafer formed on a substrate surface. An isolation trench in the wafer surface surrounds alternating p-type trenches and n-type trenches and electrically isolates the device from the substrate, thereby allowing the device to be effectively utilized as a differential detector in an optoelectronic circuit.

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